

<b>L Number</b>	<b>Hits</b>	<b>Search T xt</b>	<b>DB</b>	<b>Time stamp</b>
<b>1</b>	<b>5</b>	<b>(p lylsilicon adj tra ) and lin r and oxid and sid wall and spacer and (silic n adj nitride) and (L near (shape r shap d or shaping))</b>	<b>USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:36</b>
<b>2</b>	<b>5</b>	<b>((conductive or conducting or polysilicon) adj trace) and liner and oxide and sidewall and spacer and (silicon adj nitride) and (L near (shape or shaped or shaping))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:38</b>
<b>3</b>	<b>16</b>	<b>(gate near3 polysilicon) and (source or drain or source/drain) and liner and spacer and (silicon adj nitride) and (l near5 spacer)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:44</b>
<b>4</b>	<b>0</b>	<b>(gate near10 (source or drain or source/drain) near10 liner near10 oxide near10 (silicon adj nitride) near10 spacer near10 (l near (shape or shaped))).clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:45</b>
<b>5</b>	<b>0</b>	<b>(gate near10 (source or drain or source/drain) near10 liner near10 oxide near10 (silicon adj nitride) near10 spacer near10 (l near (shape or shaped)))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:45</b>
<b>6</b>	<b>0</b>	<b>(gate near10 (source or drain or source/drain) near10 liner near10 (insulating or dielectric or oxide) near10 (silicon adj nitride) near10 spacer near10 (l near (shape or shaped)))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:45</b>
<b>7</b>	<b>3</b>	<b>(gate same (source or drain or source/drain) same liner same (insulating or dielectric or oxide) same (silicon adj nitride) same spacer same (l near (shape or shaped)))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:48</b>
<b>8</b>	<b>7</b>	<b>(l near2 (shape or shaped) near3 spacer).clm. and liner.clm. and polysilicon.clm. and gate.clm. and (source or drain or source/drain).clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 14:59</b>
<b>9</b>	<b>21</b>	<b>(l near2 (shape or shaped) near3 spacer) and liner and polysilicon and gate and (source or drain or source/drain)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/07/07 15:00</b>